



#### 175°C P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	RDS(ON) Max	<b>Ι</b> <sub>D</sub> Τ <sub>C</sub> = +25°C
-40V	$11m\Omega$ @ V <sub>GS</sub> = -10V	-45A
	15mΩ @ V <sub>GS</sub> = -4.5V	-40A

### **Description and Applications**

This MOSFET has been designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- · Reverse Polarity Protection
- Motor Control
- Power Management

## **Features and Benefits**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMPH4015SK3Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

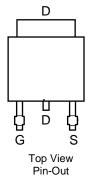
https://www.diodes.com/quality/product-definitions/

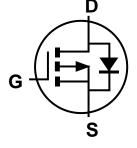
#### **Mechanical Data**

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.33 grams (Approximate)



Top View





**Equivalent Circuit** 

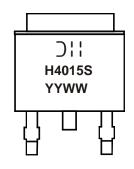
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMPH4015SK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



Ott = Manufacturer's Marking H4015S = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 20 = 2020) WW = Week (01 to 53)



#### **Maximum Ratings** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-40	V		
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current (Note C) V 10V	Steady State	T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C	ΙD	-45 -35	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +100°C	lo	-14 -10	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-100	Α		
Maximum Body Diode Forward Current (Note 6)			Is	-45	Α
Avalanche Current, L = 1mH (Note 7)	I <sub>AS</sub>	-22	Α		
Avalanche Energy, L = 1mH (Note 7)	Eas	260	mJ		

# Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	1.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	73	°C/W
Total Power Dissipation (Note 6)		PD	3.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	38	°C/W
Thermal Resistance, Junction to Case	R <sub>0</sub> JC	1.0	*C/VV	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

# Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BVDSS	-40	_		V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μΑ	V <sub>DS</sub> = -40V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(TH)	-1.5	-2	-2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	
Static Drain-Source On-Resistance	Descent	_	8	11	mΩ	$V_{GS} = -10V, I_{D} = -9.8A$	
Static Drain-Source On-Resistance	RDS(ON)	_	11	15	1117.5	$V_{GS} = -4.5V, I_{D} = -9.8A$	
Diode Forward Voltage	VsD	_	-0.7	-1	V	Vgs = 0V, Is = -1A	
DYNAMIC CHARACTERISTICS (Note 9)		•	•			•	
Input Capacitance	Ciss	_	4234	_		), oo, , , , , , , , , , , , , , , , , ,	
Output Capacitance	Coss	_	1036	_	pF	$V_{DS} = -20V, V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	Crss	_	526	_			
Gate Resistance	Rg	_	7.8	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	42.7	_			
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	91	_	nC	V <sub>DS</sub> = -20V,	
Gate-Source Charge	Qgs	_	14.2	_	lic.	$I_D = -9.8A$	
Gate-Drain Charge	Qgd	_	13.5	_			
Turn-On Delay Time	tD(ON)	_	13.2	_			
Turn-On Rise Time	t <sub>R</sub>	_	10	_		$V_{GS} = -10V, V_{DD} = -20V,$	
Turn-Off Delay Time	tD(OFF)	_	303	_	ns	$R_G = 6\Omega$ , $I_D = -1A$	
Turn-Off Fall Time	tF	_	138	_			
Reverse Recovery Time	t <sub>RR</sub>	_	26	_	ns	$I_F = -9.8A$ , di/dt = -100A/ $\mu$ s	
Reverse Recovery Charge	Qrr	_	20	_	nC	IF = -9.8A, di/dt = -100A/µs	

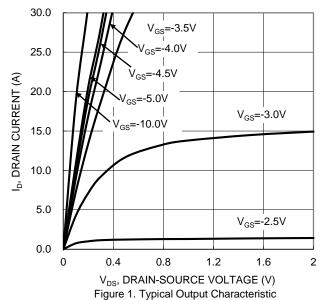
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

<sup>6.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

 <sup>7.</sup> I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.



# **DMPH4015SK3Q**



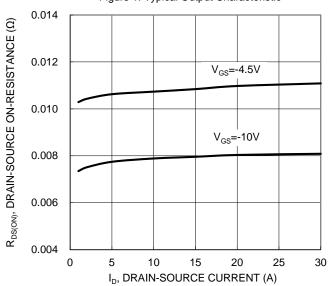


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

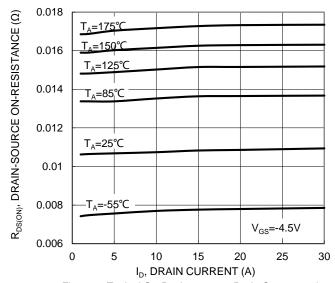


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

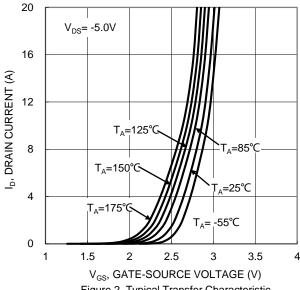


Figure 2. Typical Transfer Characteristic

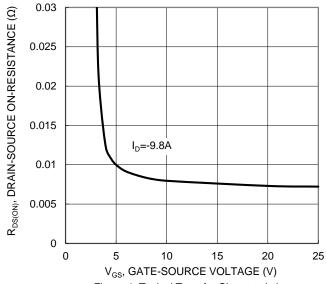


Figure 4. Typical Transfer Characteristic

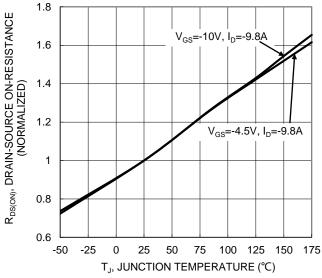


Figure 6. On-Resistance Variation with Temperature



### DMPH4015SK3Q

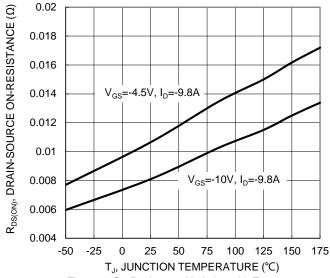


Figure 7. On-Resistance Variation with Temperature

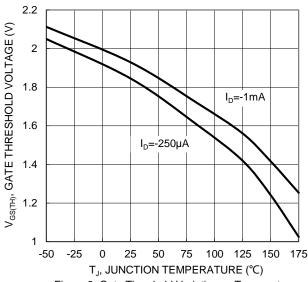


Figure 8. Gate Threshold Variation vs Temperature

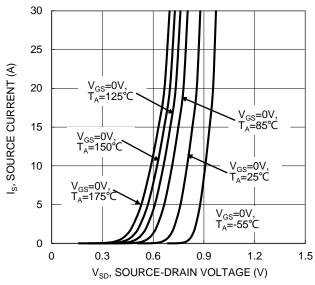
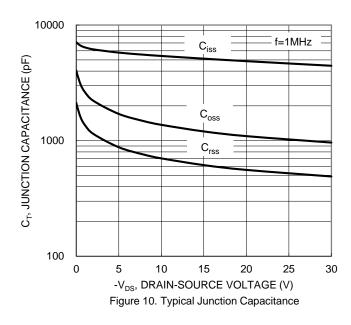


Figure 9. Diode Forward Voltage vs. Current



10 8 6  $V_{GS}(V)$ 4  $V_{DS}$ =-20V,  $I_{D}$ =-9.8A 2 0 0 20 40 60 80 100 120 Qg (nC) Figure 11. Gate Charge

1000  $R_{DS(ON)}$  LIMITED =10us 100 ID, DRAIN CURRENT (A) 10 P<sub>W</sub>=10ms  $T_{J(MAX)}$ =175°C T<sub>C</sub>=25°C Single Pulse DUT on infinite heatsink V<sub>GS</sub>=-4.5V 0.1 0.1 10 100  $V_{DS}$ , DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



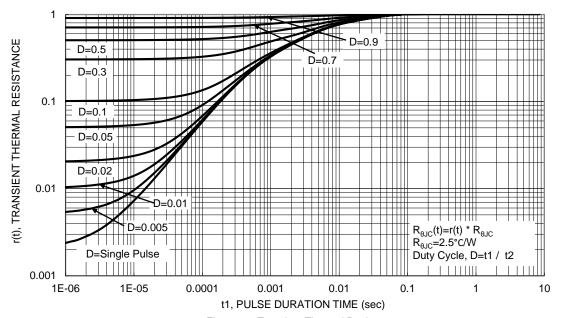


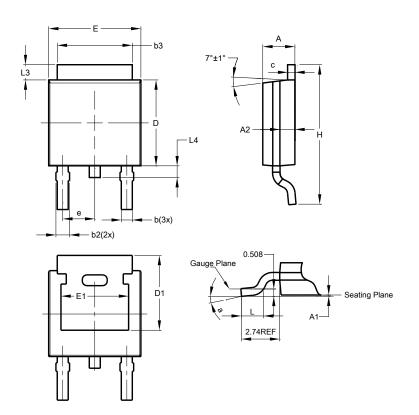
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TO252 (DPAK)

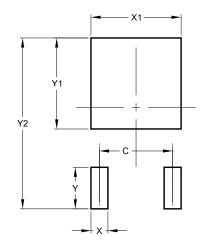


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
<b>A</b> 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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